

L Number	Hits	Search Text	DB	Time stamp
1	10717	257/68,71,295-314,324-326;438/3,240.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 11:40
2	189	257/68,71,295-314,324-326;438/3,240.ccls. and (TMR MRAM (tunnel\$3 NEAR magneto NEAR resist\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 13:10
3	98	(257/68,71,295-314,324-326;438/3,240.ccls. and (TMR MRAM (tunnel\$3 NEAR magneto NEAR resist\$3))) and ((wir\$3 bit) NEAR (line\$1 lead\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 13:06
4	1	"6515573".PN.	USPAT	2004/02/06 12:15
5	1	"6351410".PN.	USPAT	2004/02/06 12:18
6	2	("6379978"   "6473336").PN.	USPAT	2004/02/06 12:19
7	20	("5304975"   "5365212"   "5500633"   "5523172"   "5534355"   "5578385"   "5616370"   "5700588"   "5716719"   "5734605"   "5745406"   "5747859"   "5773156"   "5825685"   "5930164"   "5973334"   "6021065"   "6069820"   "6111783"   "6114056").PN.	USPAT	2004/02/06 12:29
8	1	("6211005"   "2001/0035545").PN.	USPAT	2004/02/06 12:54
9	12	("5281485"   "5341118"   "5608593"   "5640343"   "5801984"   "5841692"   "5898547"   "6097625"   "6153320"   "6174582"   "6295186"   "6297983").PN.	USPAT	2004/02/06 12:56
10	103	(257/68,71,295-314,324-326;438/3,240.ccls. and (TMR MRAM (tunnel\$3 NEAR magneto NEAR resist\$3))) and ((wir\$3 bit write) NEAR (line\$1 lead\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 13:15
11	162	257/68,71,295-314,324-326;438/3,240.ccls. and (magnetic NEAR memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 15:14
12	152	(257/68,71,295-314,324-326;438/3,240.ccls. and (magnetic NEAR memory)) and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 14:38
13	86	((257/68,71,295-314,324-326;438/3,240.ccls. and (magnetic NEAR memory)) and substrate) and transistor\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 13:09
14	49	(((257/68,71,295-314,324-326;438/3,240.ccls. and (magnetic NEAR memory)) and substrate) and transistor\$1) and (TMR MRAM (tunnel\$3 NEAR magneto NEAR resist\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 13:15
15	388805	257/\$.ccls. 438/\$.ccls. 365/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 13:14
16	2033	(257/\$.ccls. 438/\$.ccls. 365/\$.ccls.) and (magnetic NEAR memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 13:14

17	299	((257/\$.ccls. 438/\$.ccls. 365/\$.ccls.) and (magnetic NEAR memory)) and (substrate WITH transistor\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 13:15
18	151	((257/\$.ccls. 438/\$.ccls. 365/\$.ccls.) and (magnetic NEAR memory)) and (substrate WITH transistor\$1)) and (TMR MRAM (tunnel\$3 NEAR magneto NEAR resist\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 14:38
19	134	(((257/\$.ccls. 438/\$.ccls. 365/\$.ccls.) and (magnetic NEAR memory)) and (substrate WITH transistor\$1)) and (TMR MRAM (tunnel\$3 NEAR magneto NEAR resist\$3))) and ((wir\$3 bit write) NEAR (line\$1 lead\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 14:39
20	0	(257/\$.ccls. 438/\$.ccls. 365/\$.ccls.) and (((wir\$3 write) NEAR (line\$1 lead\$1)) WITH (width length) WITH (greater longer) WITH (TMS (magneto NEAR resist\$5)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 14:36
21	2	(257/\$.ccls. 438/\$.ccls. 365/\$.ccls.) and ((wir\$3 write) NEAR (line\$1 lead\$1)) and ((width length) WITH (greater longer) WITH (TMS (magneto NEAR resist\$5)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 14:37
22	1704	(257/\$.ccls. 438/\$.ccls. 365/\$.ccls.) and (TMR MRAM (magneto NEAR resist\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 15:14
23	292	((257/\$.ccls. 438/\$.ccls. 365/\$.ccls.) and (TMR MRAM (magneto NEAR resist\$5))) and (substrate WITH transistor\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 15:44
24	233	(((257/\$.ccls. 438/\$.ccls. 365/\$.ccls.) and (TMR MRAM (magneto NEAR resist\$5))) and (substrate WITH transistor\$1)) and ((wir\$3 bit write) NEAR (line\$1 lead\$1)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 14:40
25	149	(((257/\$.ccls. 438/\$.ccls. 365/\$.ccls.) and (TMR MRAM (magneto NEAR resist\$5))) and (substrate WITH transistor\$1)) and ((wir\$3 bit write) NEAR (line\$1 lead\$1))) and (width length)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 14:40
26	237	(((257/\$.ccls. 438/\$.ccls. 365/\$.ccls.) and (TMR MRAM (magneto NEAR resist\$5))) and (substrate WITH transistor\$1)) and ((wir\$3 bit metal write) NEAR (line\$1 lead\$1)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 15:15
27	150	(((257/\$.ccls. 438/\$.ccls. 365/\$.ccls.) and (TMR MRAM (magneto NEAR resist\$5))) and (substrate WITH transistor\$1)) and ((wir\$3 bit metal write) NEAR (line\$1 lead\$1))) and (width length)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 16:37
28	98	((((257/\$.ccls. 438/\$.ccls. 365/\$.ccls.) and (TMR MRAM (magneto NEAR resist\$5))) and (substrate WITH transistor\$1)) and ((wir\$3 bit metal write) NEAR (line\$1 lead\$1))) and (width length)) and (magnetic NEAR memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 16:36

29	12987	magnetic NEAR memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 15:14
30	1267	(magnetic NEAR memory) and (TMR MRAM (magneto NEAR resist\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 18:00
31	173	((magnetic NEAR memory) and (TMR MRAM (magneto NEAR resist\$5))) and (substrate WITH transistor\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 17:35
32	152	((magnetic NEAR memory) and (TMR MRAM (magneto NEAR resist\$5))) and (substrate WITH transistor\$1)) and ((wir\$3 bit metal write) NEAR (line\$1 lead\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 15:43
33	4	("5374578"   "5389566"   "5567636"   "5659499").PN.	USPAT	2004/02/06 15:40
34	694	(TMR MRAM (magneto NEAR resist\$5)) WITH ((wir\$3 bit metal write) NEAR (line\$1 lead\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 16:32
35	347	((TMR MRAM (magneto NEAR resist\$5)) WITH ((wir\$3 bit metal write) NEAR (line\$1 lead\$1))) and (magnetic NEAR memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 15:44
36	106	((TMR MRAM (magneto NEAR resist\$5)) WITH ((wir\$3 bit metal write) NEAR (line\$1 lead\$1))) and (magnetic NEAR memory)) and (substrate WITH transistor\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 16:36
37	701	(TMR MRAM (magneto NEAR resist\$5)) WITH (((wir\$3 bit metal write) (write NEAR word)) NEAR (line\$1 lead\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 16:36
38	352	((TMR MRAM (magneto NEAR resist\$5)) WITH (((wir\$3 bit metal write) (write NEAR word)) NEAR (line\$1 lead\$1))) and (magnetic NEAR memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 18:24
39	110	((TMR MRAM (magneto NEAR resist\$5)) WITH (((wir\$3 bit metal write) (write NEAR word)) NEAR (line\$1 lead\$1))) and (magnetic NEAR memory)) and (substrate WITH transistor\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 16:36
40	71	(((TMR MRAM (magneto NEAR resist\$5)) WITH (((wir\$3 bit metal write) (write NEAR word)) NEAR (line\$1 lead\$1))) and (magnetic NEAR memory)) and (substrate WITH transistor\$1)) and (width length)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 16:37
41	0	10/615920	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 17:39

42	16248	(TMR MRAM (magneto NEAR resist\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 18:01
43	0	((TMR MRAM (magneto NEAR resist\$5))) and (step NEAR like NEAR difference)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 18:02
44	55	((TMR MRAM (magneto NEAR resist\$5))) and (step NEAR like)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 18:23
45	275	((TMR MRAM (magneto NEAR resist\$5))) and misalignment	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 18:23
46	49	((((TMR MRAM (magneto NEAR resist\$5))) and misalignment) and (magnetic NEAR memory))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 18:24
47	8	("5732016"   "5838608"   "5949707"   "5956267"   "5982658"   "5982660"   "6005800"   "6072717").PN.	USPAT	2004/02/06 18:44